

این دیتاشیت توسط توکل الکترونیک تهیه و ارائه شده است.
جهت مشاهده قیمت، موجودی و ثبت سفارش این قطعه به وبسایت توکل الکترونیک مراجعه فرمایید.



مشاهده قیمت و خرید

برای خرید و مشاهده سایر محصولات کلیک کنید



SHINDENGEN

VZ Series Power MOSFET

N-Channel Enhancement type

2SK2492
(F20F18VZ)

180V 20A

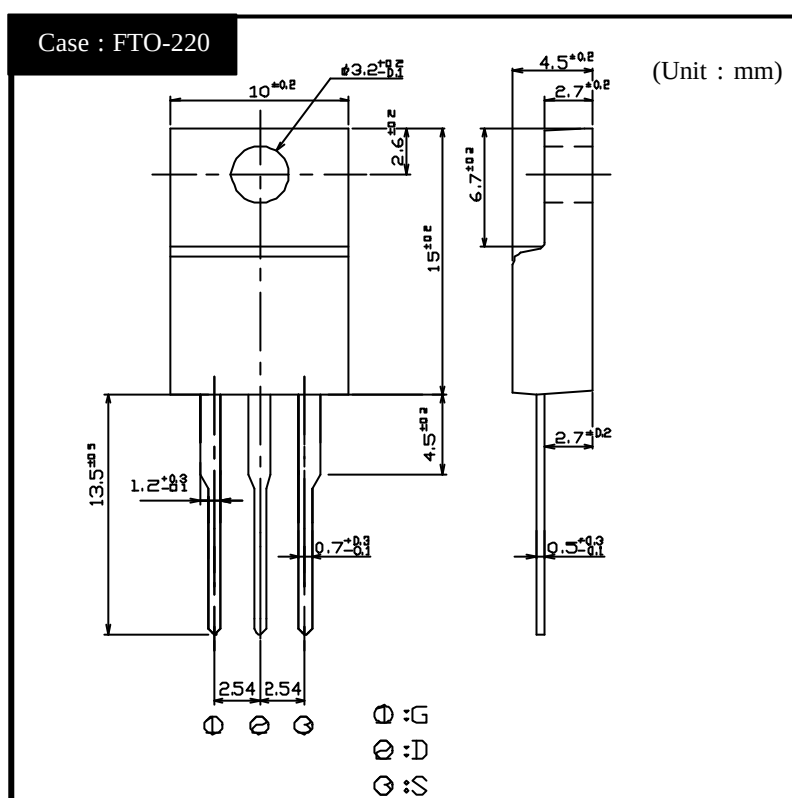
FEATURES

- Input capacitance (Ciss) is small.
Especially, input capacitance at 0 bias is small.
- The static Rds(on) is small.
- The switching time is fast.

APPLICATION

- DC/DC converters
- Power supplies of DC 12-24V input
- Product related to
Integrated Service Digital Network

OUTLINE DIMENSIONS



RATINGS

● Absolute Maximum Ratings (Tc = 25°C)

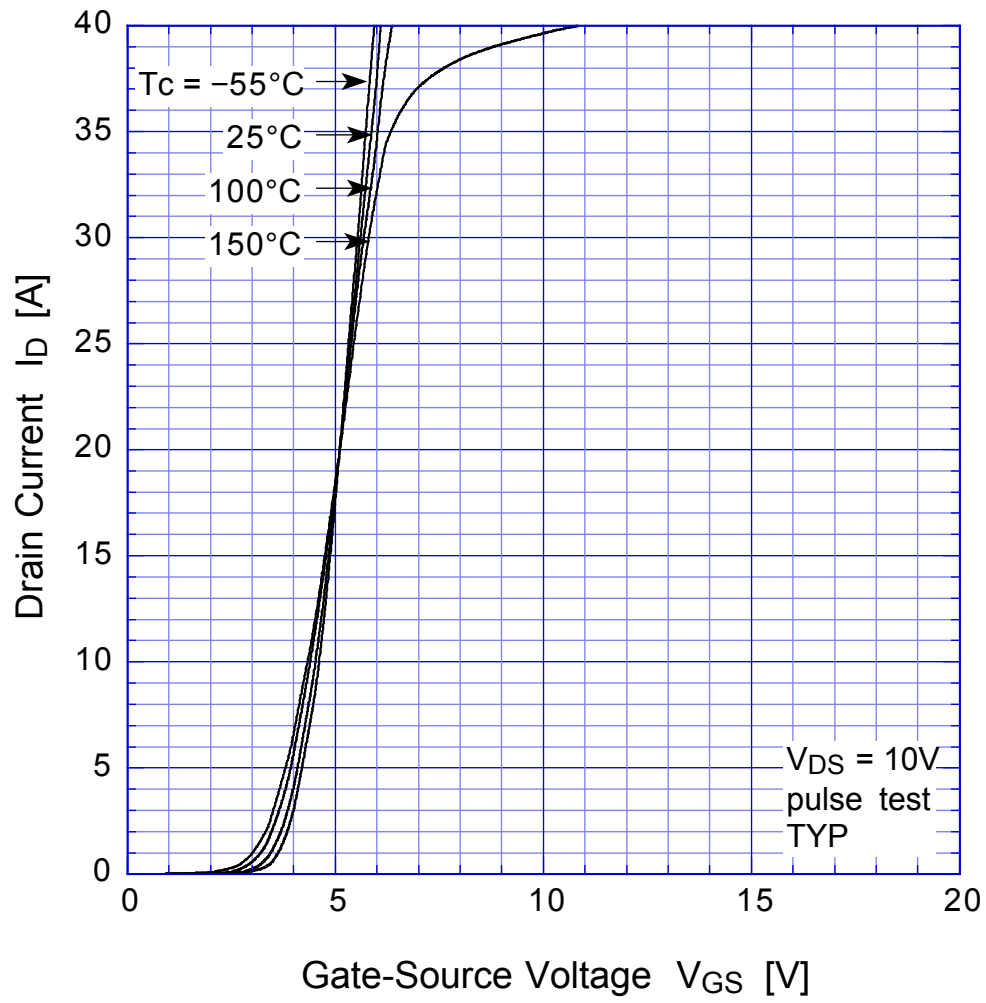
Item	Symbol	Conditions	Ratings	Unit
Storage Temperature	T _{stg}		-55~150	°C
Channel Temperature	T _{ch}		150	
Drain-Source Voltage	V _{DSS}		180	V
Gate-Source Voltage	V _{GSS}		±30	
Continuous Drain Current (DC)	I _D		20	A
Continuous Drain Current (Peak)	I _{DP}		40	
Continuous Source Current (DC)	I _S		20	
Total Power Dissipation	P _T		60	W
Single Pulse Avalanche Current	I _{AS}	T _{ch} = 25°C	20	A
Mounting Torque	TOR	(Recommended torque 0.3 N·m)	0.5	N·m

●Electrical Characteristics $T_c = 25^\circ\text{C}$

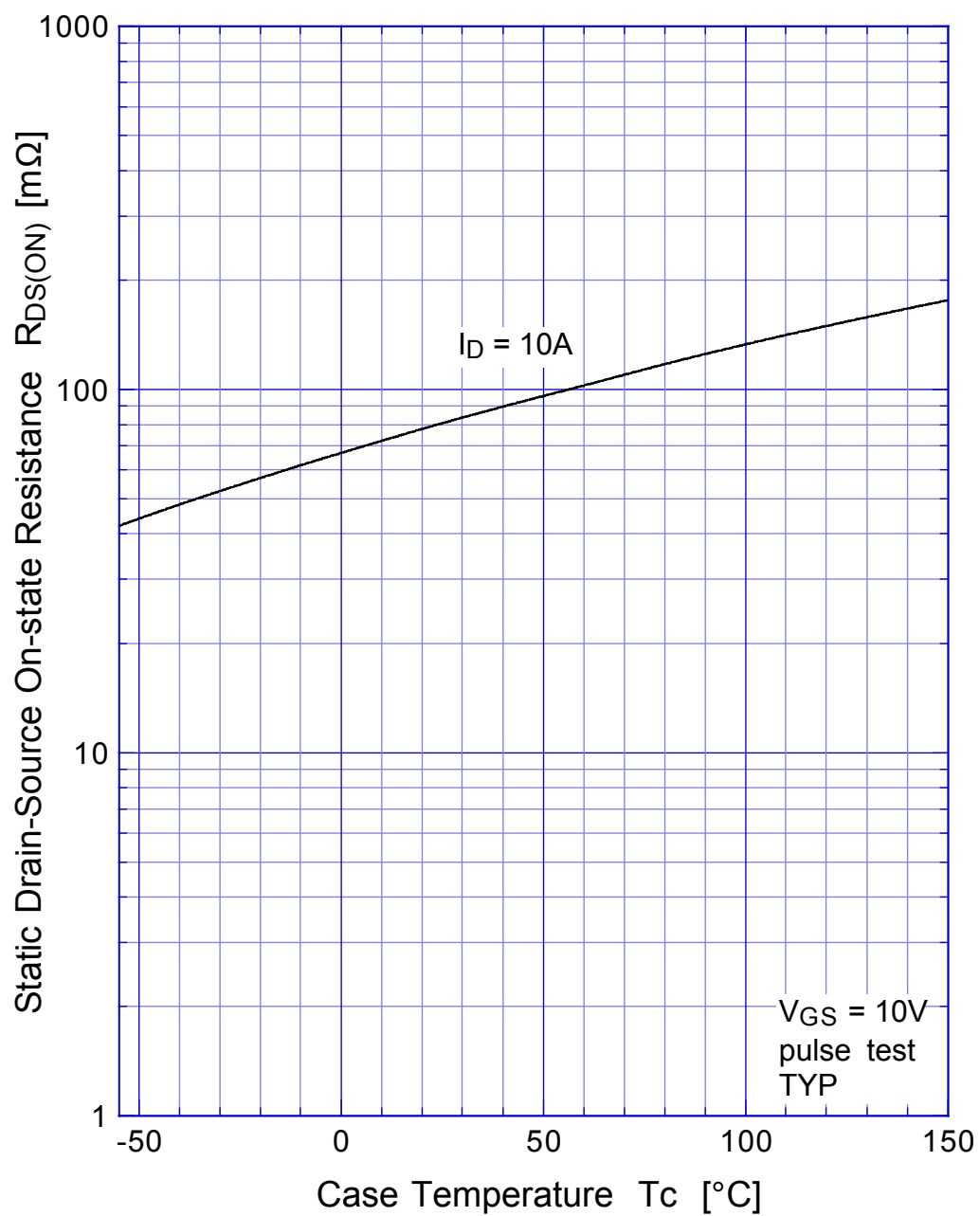
Item	Symbol	Conditions	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D = 1\text{mA}$, $V_{GS} = 0\text{V}$	180			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 180\text{V}$, $V_{GS} = 0\text{V}$			250	μA
Gate-Source Leakage Current	I_{GSS}	$V_{GS} = \pm 30\text{V}$, $V_{DS} = 0\text{V}$			± 0.1	
Forward Transconductance	g_{fs}	$I_D = 10\text{A}$, $V_{DS} = 10\text{V}$	8	15		S
Static Drain-Source On-state Resistance	$R_{DS(ON)}$	$I_D = 10\text{A}$, $V_{GS} = 10\text{V}$		0.08	0.13	Ω
Gate Threshold Voltage	V_{TH}	$I_D = 1\text{mA}$, $V_{DS} = 10\text{V}$	2.0	3.0	4.0	V
Source-Drain Diode Forward Voltage	V_{SD}	$I_S = 10\text{A}$, $V_{GS} = 0\text{V}$			1.5	
Thermal Resistance	θ_{jc}	junction to case			2.08	$^\circ\text{C}/\text{W}$
Total Gate Charge	Q_g	$V_{DD} = 150\text{V}$, $V_{GS} = 10\text{V}$, $I_D = 20\text{A}$		55		nC
Input Capacitance	C_{iss}	$V_{DS} = 10\text{V}$, $V_{GS} = 0\text{V}$, $f = 1\text{MHz}$		1600		pF
Reverse Transfer Capacitance	C_{rss}			190		
Output Capacitance	C_{oss}			650		
Turn-On Time	t_{on}	$I_D = 10\text{A}$, $V_{GS} = 10\text{V}$, $R_L = 10\Omega$		95	190	ns
Turn-Off Time	t_{off}			300	600	

2SK2492

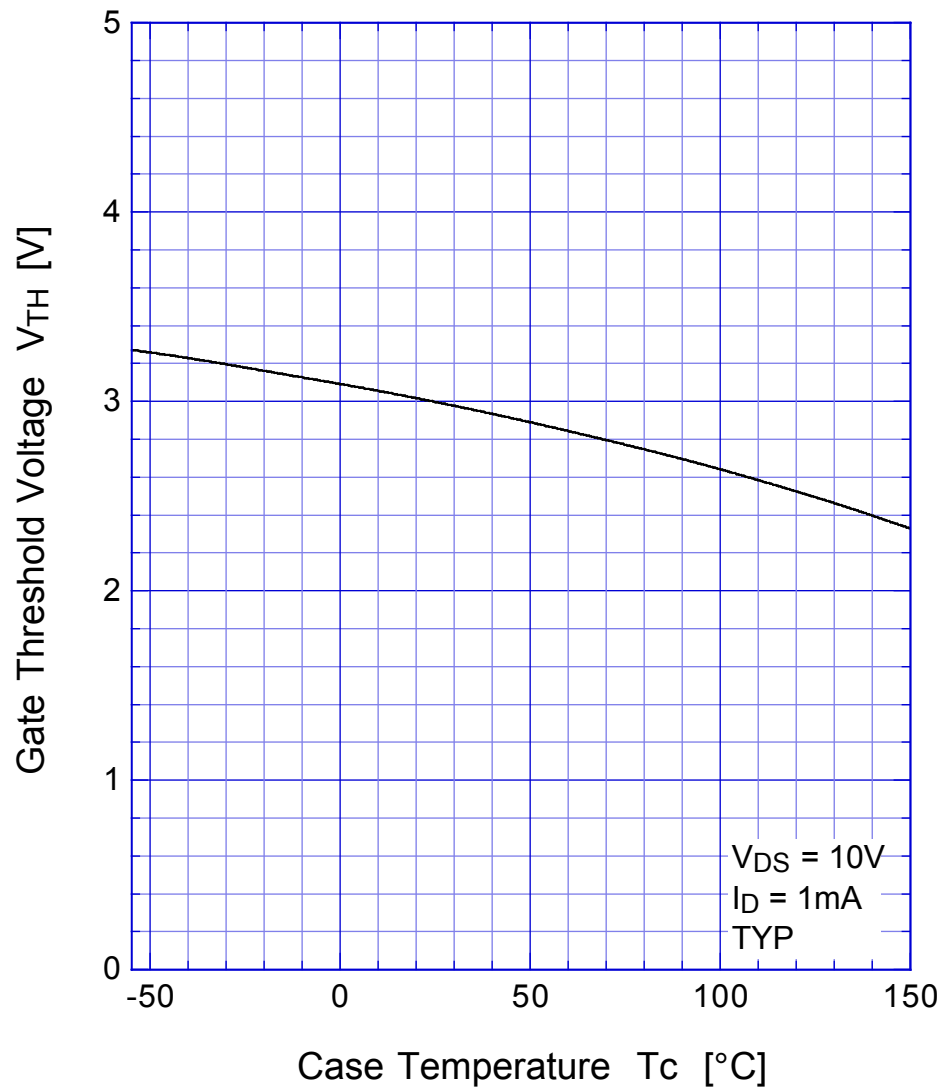
Transfer Characteristics



2SK2492 Static Drain-Source On-state Resistance

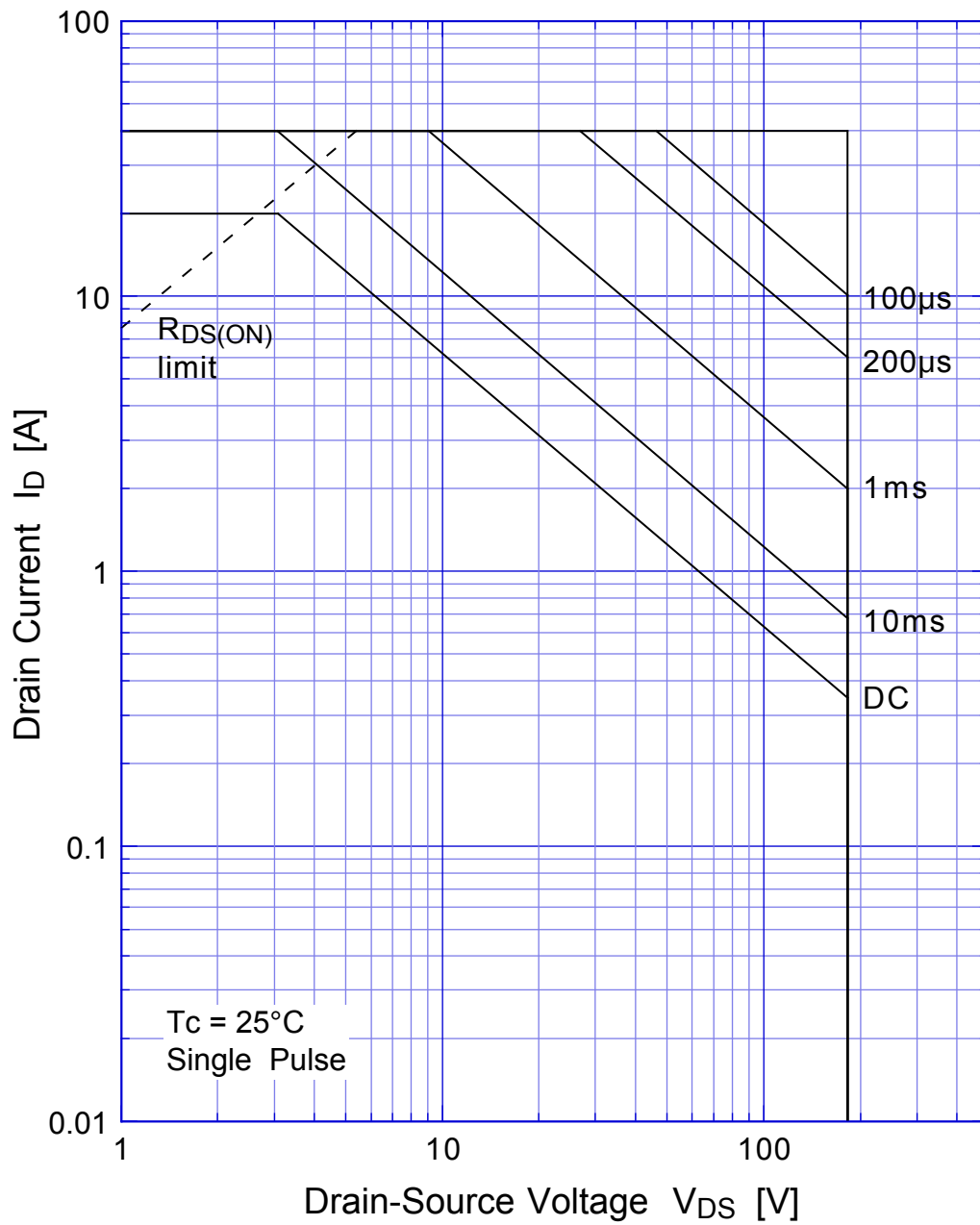


2SK2492 Gate Threshold Voltage

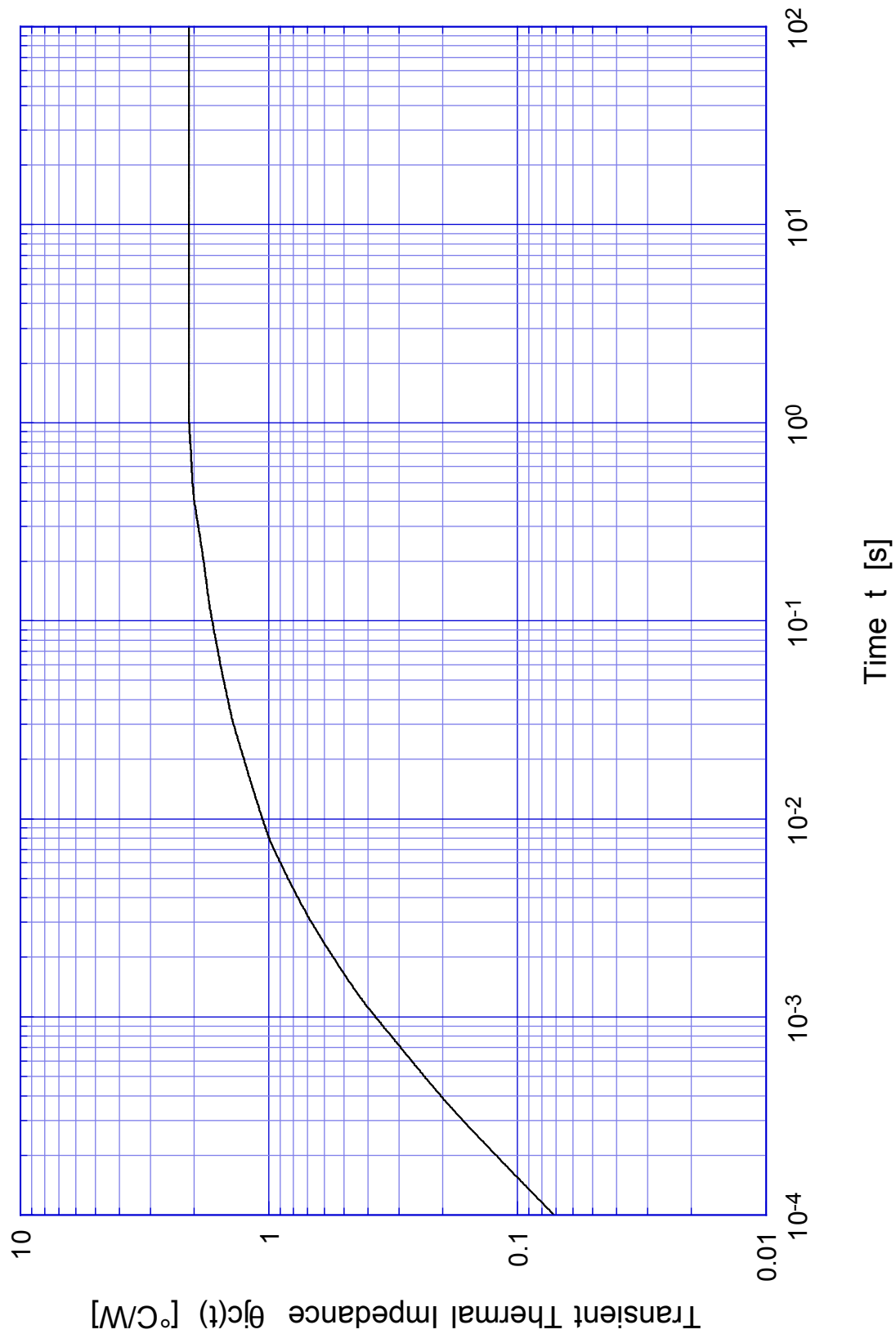


2SK2492

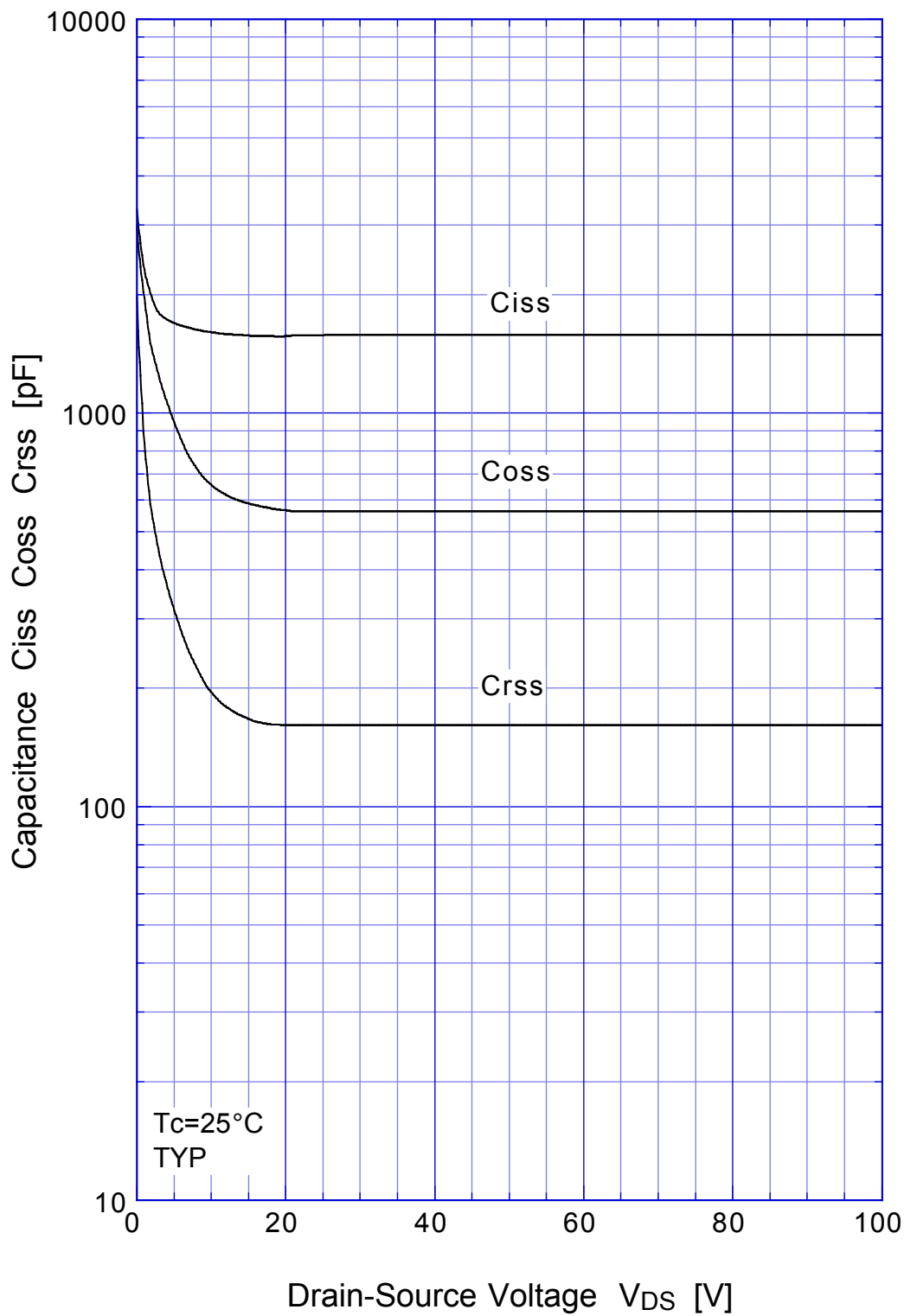
Safe Operating Area



2SK2492 Transient Thermal Impedance

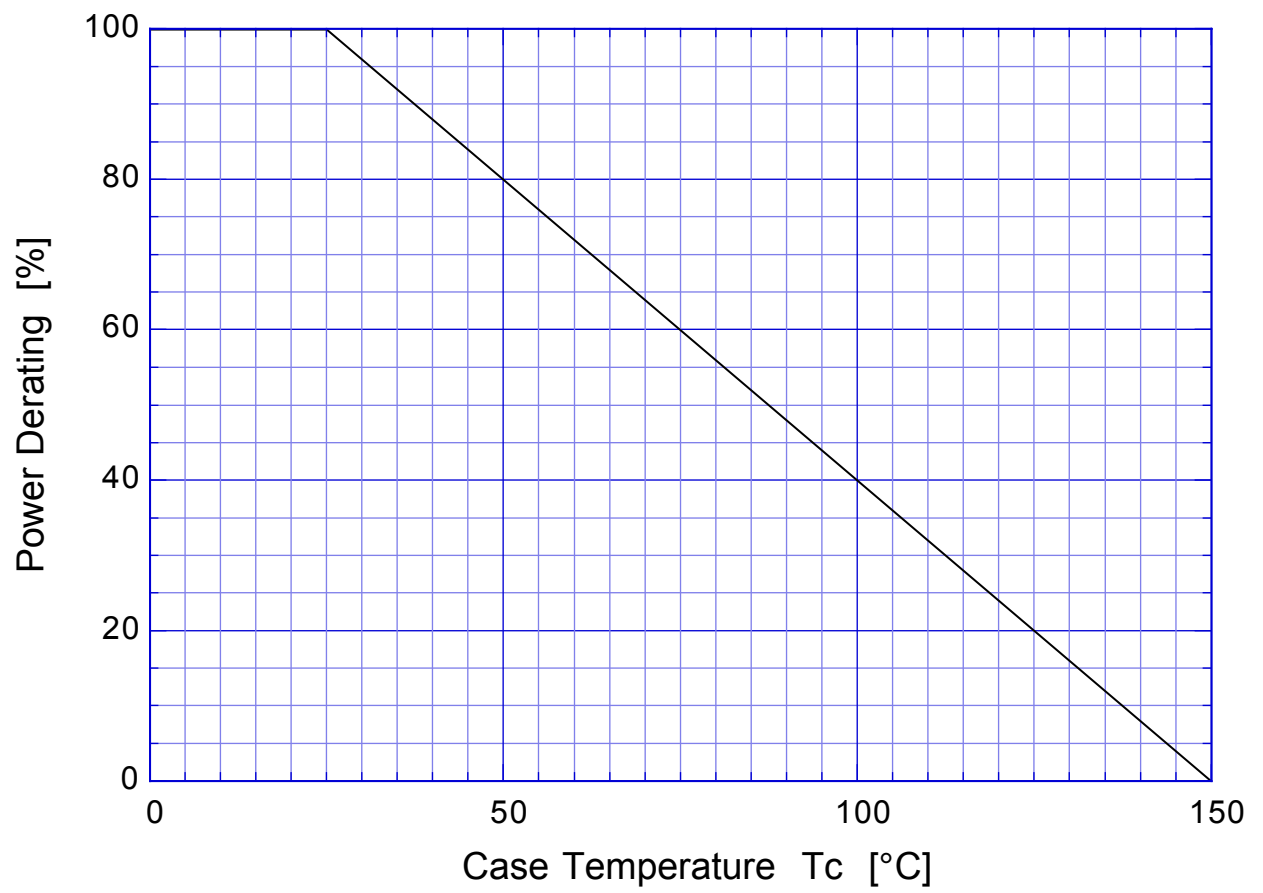


2SK2492 Capacitance



2SK2492

Power Derating



2SK2492

Gate Charge Characteristics

